

FORM: PTO-1449 (REV: 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	Atty Docket No: 2000-0719.01/US	Serial No: Not Assigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Applicant: Micron Technology, Inc.	
(use several sheets if necessary)		Filing Date: September 8, 2003	Group: Not Assigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass
AA	5,852,307	12/1998	Aoyama et al.	257	285
AB	6,037,206	03/2000	Huang et al.	438	240
AC	6,278,152	08/2001	Hieda et al.	257	306
AD	6,284,587	09/2001	Yamauchi et al.	438	240
AE	6,475,854	11/2002	Narwankar et al.	438	238
AF	US 2002/0037630	03/2002	Agarwal et al.	438	460
AG					
AH					
AI					
AJ					
AK					

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
AL						<input type="checkbox"/>	<input type="checkbox"/>
AM						<input type="checkbox"/>	<input type="checkbox"/>
AN						<input type="checkbox"/>	<input type="checkbox"/>

Initial / OTHER ART (including author, title, date, pertinent pages, etc.)

Initial /	AO	"In-situ Barrier Formation for High Reliable W/Barrier/poly-Si Gate Using Denudation of WNX on Polycrystalline Si", Byung Hak Lee et al., R & D Division, LG Semicon Co. Ltd., 1 Hyangjeong-dong, Cheongju-si, 361-480, Korea, 9/98.										
		"Tungsten Gate Structure Formed by Reduced Temperature Conversion of Tungsten Nitride", C.J. Galewski et al., Genus Inc. pp 1-2	no data available									
Initial /	AQ	Copending Application: "Method for Forming and Integrated Circuit Structures Containing Ruthenium and Tungsten Containing Layers", Serial Number 09/590,795, Docket Number 6047-53173, Filed June 8, 2000.										
Initial /	AR	NOT A PUBLICATION										

Examiner: <i>[Signature]</i>	Date Considered: <i>6/7/03</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.